

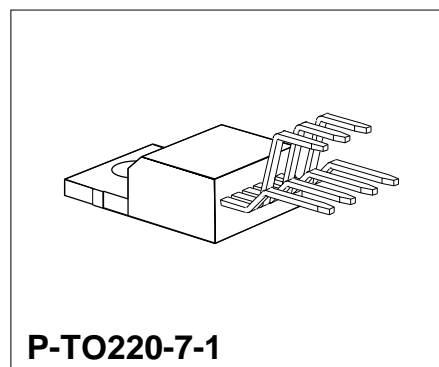
## Intelligent Double Low-Side Switch 2 × 2 A

TLE 4211

Bipolar IC

### Features

- Double low-side switch, 2 x 2 A
- Power limitation
- Overtemperature shutdown
- Status monitoring
- Shorted-load protection
- Reverse polarity protection
- Integrated clamp Z-Diodes
- Voltage proof up to 70 V
- Temperature range – 40 to 125 °C



Type	Ordering Code	Package
TLE 4211	Q67000-A8118	P-TO220-7-1

### Application

Applications in automotive electronics require intelligent power switches activated by logic signals, which are shorted-load protected and provide error feedback.

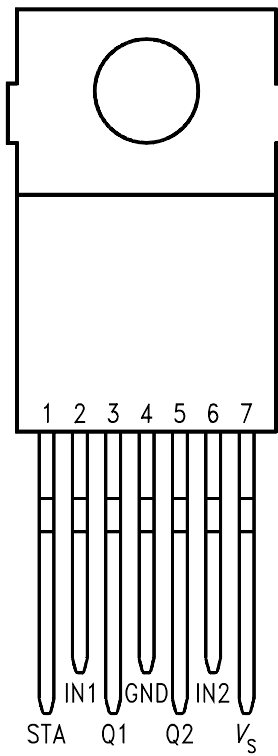
The IC contains two of these power switches (low-side switch). In case of inductive loads the integrated power Z-diodes clamp the discharging voltage.

With TTL signals at the control inputs (active low) both switches can be activated independently of one another. If one of the inputs is not in use, it must be applied to high potential.

The status output (open collector) signals the following malfunctions through low potential:

- Overload,
- Open load,
- Output shorted to ground,
- Overvoltage.

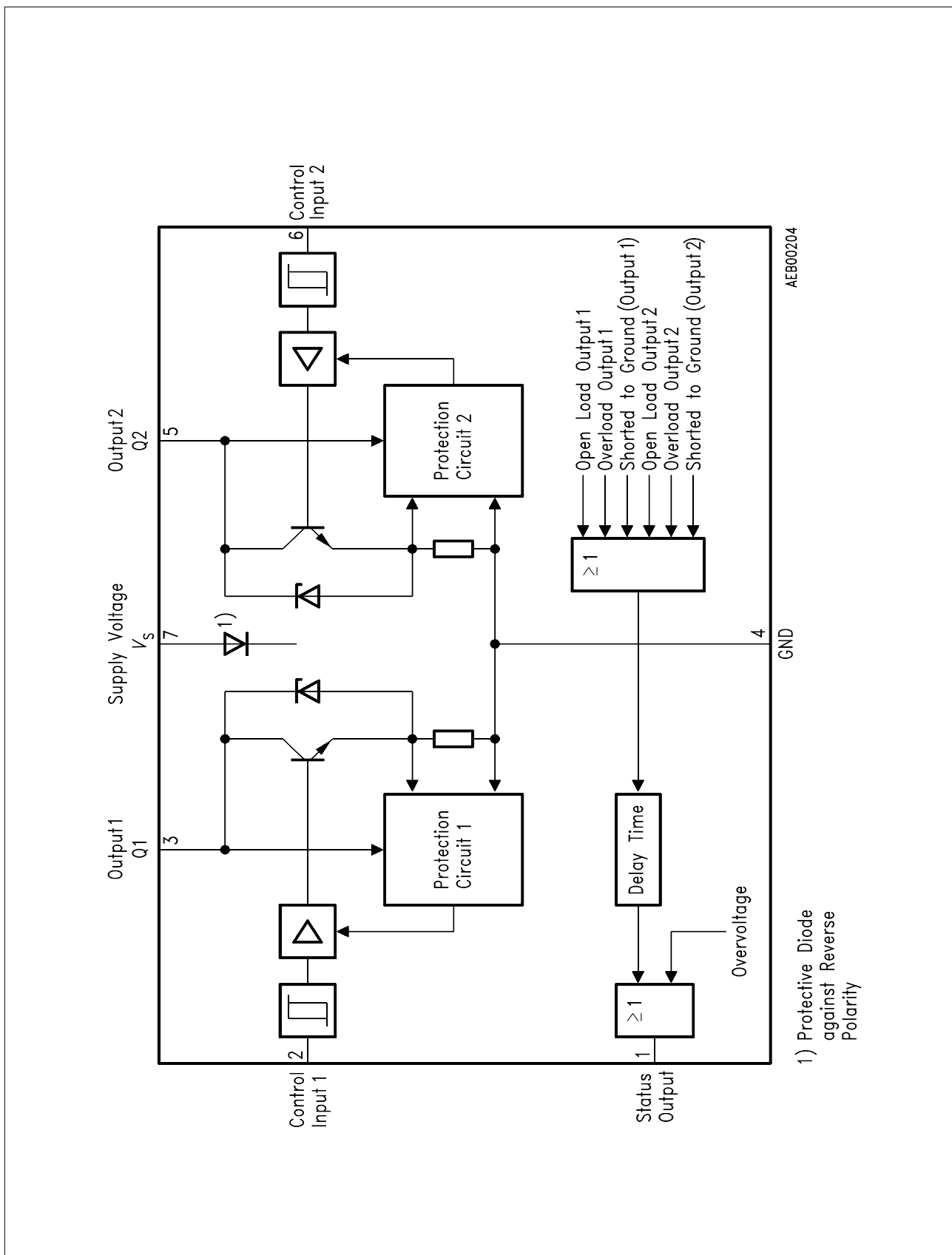
## Pin Configuration (top view)



AEP00203

### Pin Definitions and Functions

Pin No.	Symbol	Function
1	STA	<b>Status output (open collector)</b> for both outputs; indicates overload, open load and shorted load to ground as well as overvoltage at pin 7. In case of malfunction the status output is switched to low after a delay time (except overvoltage).
2	IN1	<b>Control input 1 (TTL-compatible)</b> activates output transistor 1 in case of low-potential.
3	Q1	<b>Output 1</b> Shorted-load protected, open collector output with 36 V clamp Z-diode to ground.
4	GND	<b>Ground</b> Wiring must be designed for a max. short-circuit current (2 x 3.5 A).
5	Q2	<b>Output 2</b> Shorted-load protected, open collector output with 36 V clamp Z-diode to ground.
6	IN2	<b>Control input 2 (TTL-compatible)</b> activates output transistor 2 in case of low-potential.
7	$V_s$	<b>Supply voltage</b> In case of overvoltage at this pin large sections of the circuit are deactivated. The status output indicates the malfunction without delay time.



Block Diagram

## Circuit Description

### Input Circuits

The control inputs comprise TTL-compatible Schmitt triggers with hysteresis. Driven by these stages the inverting buffer amplifiers convert the logic signal for driving the NPN power transistors.

### Switching Stages

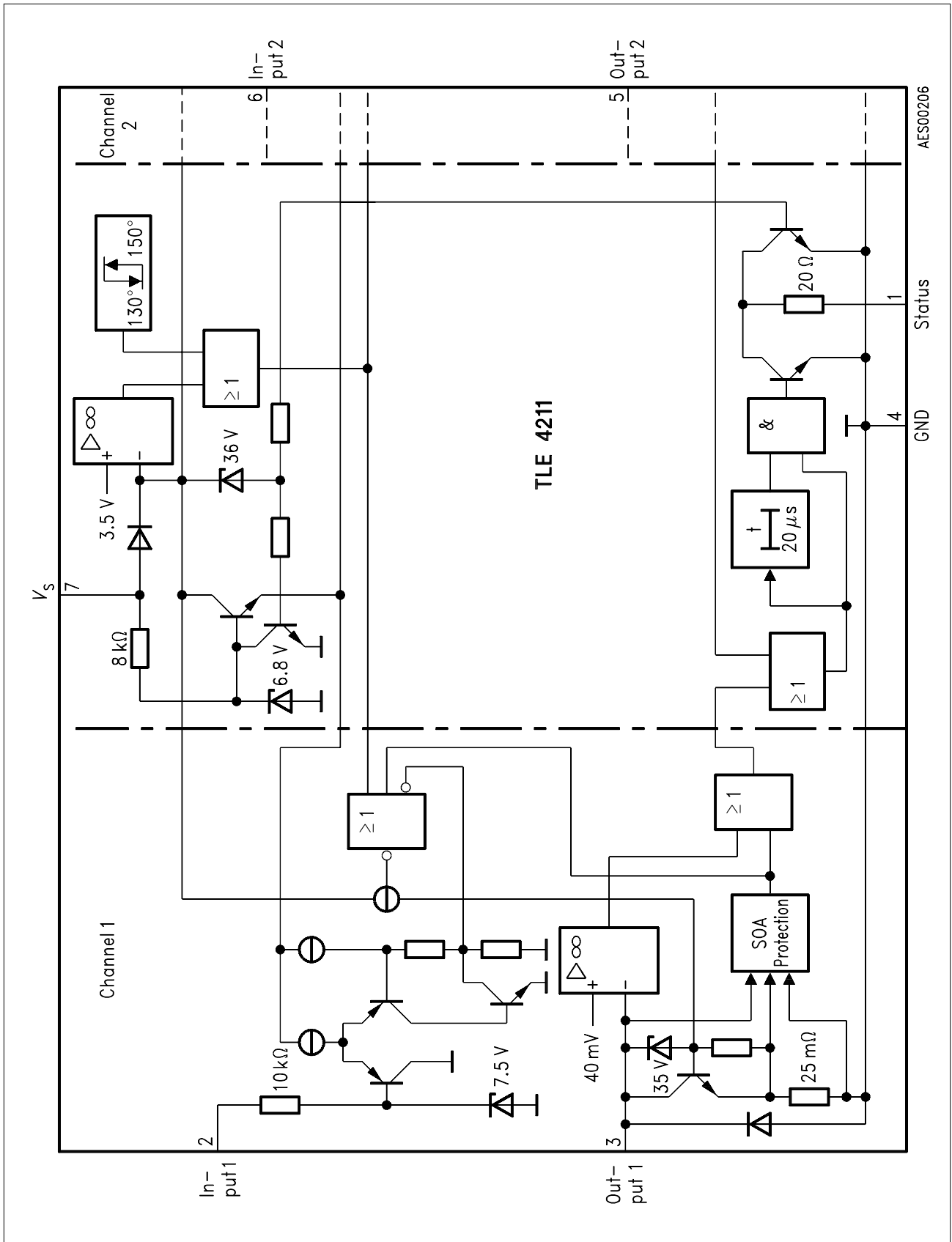
The output stages comprise NPN power transistors with open collectors. Since the protective circuit allocated to each stage limits the power dissipation, the outputs are shorted-load protected to the supply voltage throughout the entire operating range. Positive voltage peaks, which occur during the switching of inductive loads, are limited by the integrated clamp Z-diodes.

### Monitoring and Protective Functions

The outputs are monitored for open load, overload, and shorted output to ground (**see table below**). In addition, large sections of the circuit are de-activated in case of excessive supply voltages  $V_S$ . Linked via OR gate the information regarding these malfunctions effects the status output (open collector, active low). An internally determined delay time applied to all malfunctions but overvoltage prevents the output of messages in case of short-term malfunctions. Furthermore, a temperature protection circuit prevents thermal overload. An integrated reverse diode protects the supply voltage  $V_S$  against reverse polarities. Similarly the load circuit is protected against reverse polarities within the limits established by the maximum ratings (no shorted load at the same time!). At supply voltages below the operating range an undervoltage detector ensures that neither the status nor the outputs are activated.

**Status Output (L = Error)**

	Undervoltage	Operating Range		Overvoltage
		$V_I = L$ (active)	$V_I = H$ (passive)	
Normal function	H	H	H	L
Overload	H	L	H	L
Open load	H	L	H	L
Shorted output to ground	H	L	L	L



Circuit Diagram

## Absolute Maximum Ratings

$$T_j = -40 \text{ to } 150 \text{ } ^\circ\text{C}$$

Parameter	Symbol	Limit Values		Unit
		min.	max.	

## Voltages

Supply voltage (pin 7) <sup>1)</sup>	$V_S$	-45	45	V
Supply voltage (pin 7) $t \leq 500 \text{ ms}$	$V_S$	-	70	V
Input voltage (pin 2; pin 6)	$V_I$	-5	45	V
Output voltage (pin 1)	$V_O$	-0.3	45	V

## Currents

Switching current (pin 3; pin 5)	$I_Q$	limited internally		
Current with reverse polarity (pin 3; pin 5) $T_C \leq 85 \text{ } ^\circ\text{C}$	$I_Q$	-2.2	-	A
Output current (pin 1)	$I_Q$	-	10	mA
Max. current at inductive load	$I_Q$	-	see Diagram	
Junction temperature	$T_j$	-	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-50	150	$^\circ\text{C}$

## Operating Range

Supply voltage	$V_S$	5.6 <sup>2)</sup>	20	V
Supply voltage slew rate	$dV_S/dV$	-1	1	V/ $\mu\text{s}$
Case temperature	$T_C$	-40	125	$^\circ\text{C}$
Thermal resistance junction to case	$R_{th \text{ JC}}$	-	4	K/W
junction to ambient	$R_{th \text{ JA}}$	-	65	K/W

<sup>1)</sup> Refer to monitoring and protective functions

<sup>2)</sup> Lower limit = 4.6 V, if previously  $V_S$  greater than 5.6 V (turn-on hysteresis)

## Characteristics

$V_S = 6$  to  $18$  V and  $T_j = -40$  to  $125$  °C

Parameter	Symbol	Limit Values			Unit	Test Condition
		min.	typ.	max.		

## General Characteristics

Quiescent current	$I_S$	–	3.5	10	mA	$V_1 = V_1 > V_{IH}$
Supply voltage	$I_S$	–	100	180	mA	$V_1 = V_1 < V_{IL}$
Supply overvoltage shutdown threshold	$V_{SO}$	34	36	42	V	$I_O = 5$ mA; $V_O < 0.4$ V
Open load error threshold voltage	$V_{QU}$	–	40	–	mV	$I_O = 5$ mA; $V_O < 0.4$ V
Open load error threshold current	$I_{QU}$	–	50	120	mA	$V_Q = V_{QU}$
Open load error threshold current for both channels active	$I_{QU}$	–	–	250	mA	$V_{Q1} = V_{Q2} = V_{QU}$

## Logic

Control input						
H-input voltage	$V_{IH}$	–	1.7	2.4	V	–
L-input voltage	$V_{IL}$	0.7	1.1	–	V	–
Hysteresis of input voltage	$\Delta V_1$	–	0.6	–	V	–
H-input current	$I_{IH}$	–	–	10	μA	$V_1 = 5$ V
L-input current	$-I_{IL}$	–	–	10	μA	$V_1 = 0.5$ V
Status output (open coll.)						
L-saturation voltage	$V_{OSat}$	–	–	0.4	V	$I_O = 5$ mA
Status delay time	$t_{dS}$	12	20	30	μs	<sup>1)</sup>

<sup>1)</sup> Period from the beginning of the disturbance at one channel (exception: overvoltage) until the 50 % value of the status switching edge is reached.



## Characteristics (cont'd)

$V_S = 6$  to  $18$  V and  $T_j = -40$  to  $125$  °C

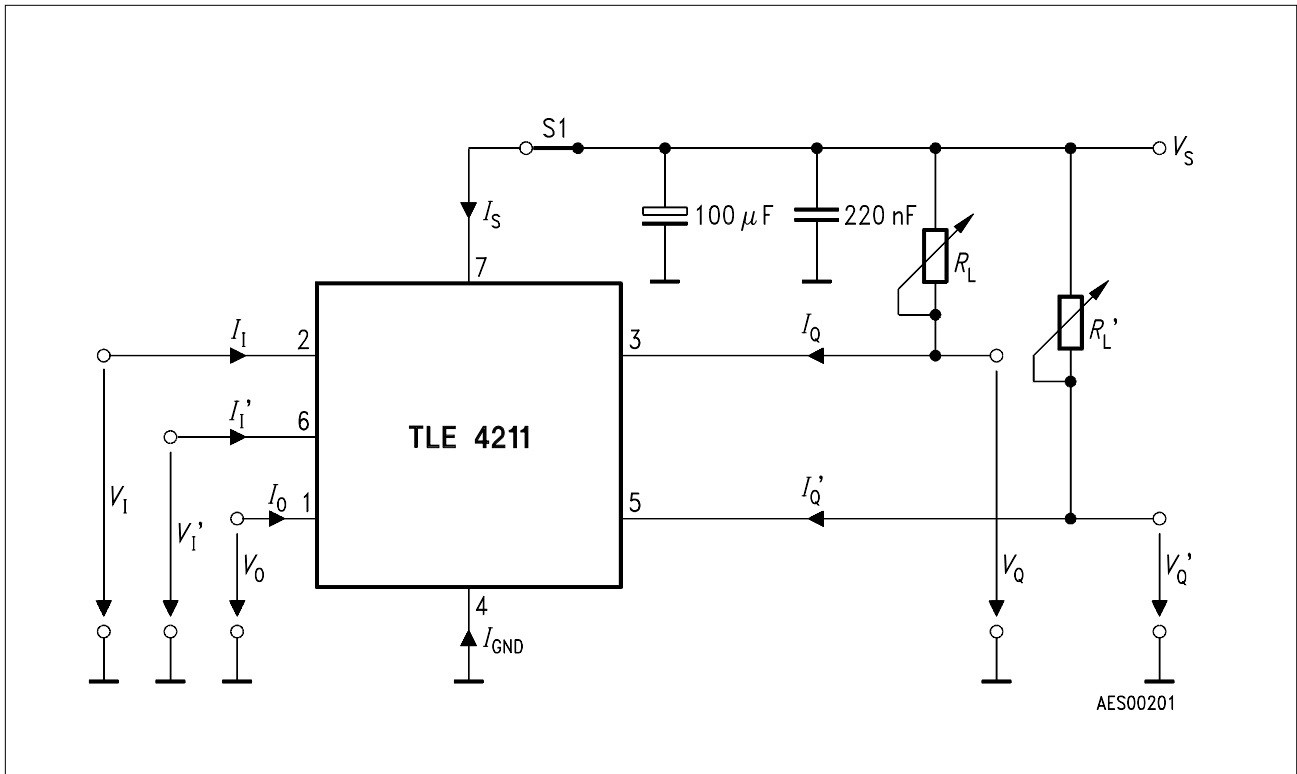
Parameter	Symbol	Limit Values			Unit	Test Condition
		min.	typ.	max.		

## Power Output

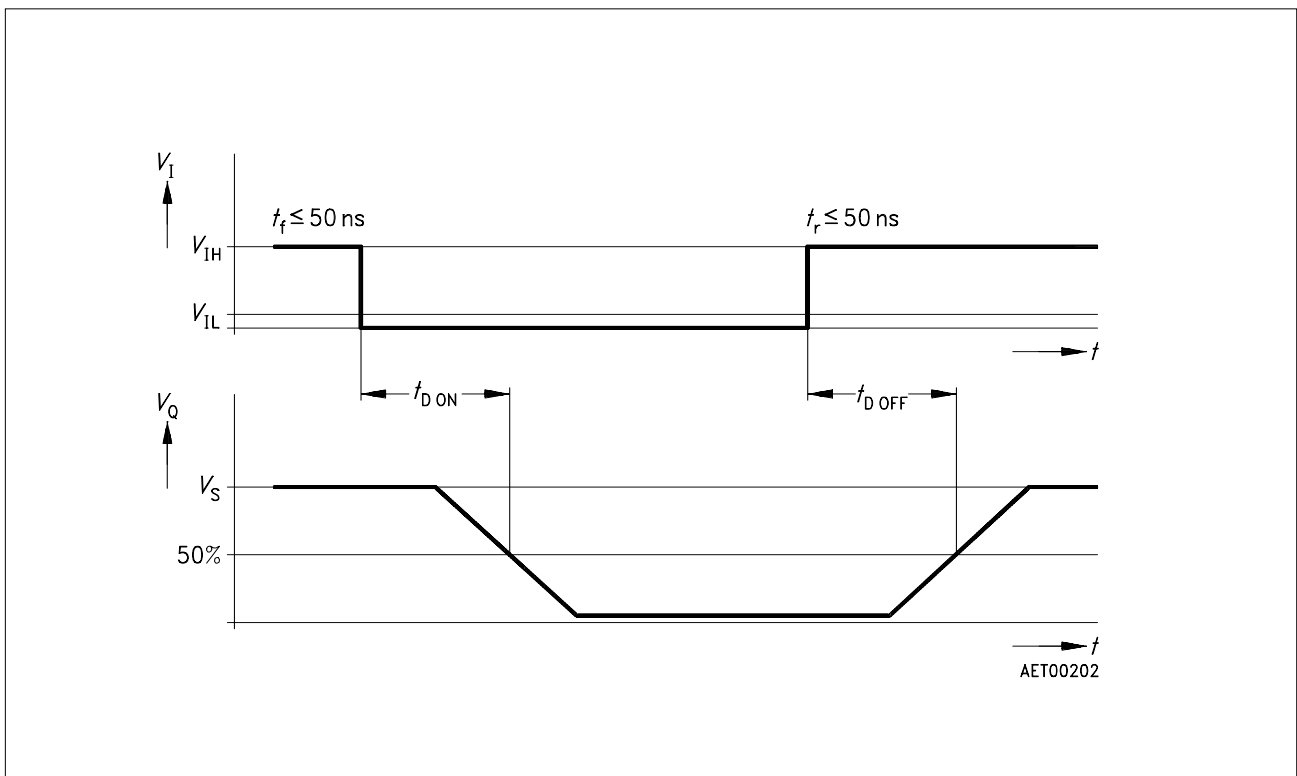
Saturation voltage	$V_{QSat}$	–	0.6	0.8	V	$I_Q = 1.6$ A; $V_I < V_{IL}$ ; $T_j = 25$ °C
Leakage current	$I_Q$	–	–	300	μA	$V_Q = 6$ V; $V_I > V_{IH}$
Switch-ON time	$t_{D ON}$	–	0.5	5	μs	<b>see Timing Diagram;</b> $I_Q = 1$ A
Switch-OFF time	$t_{D OFF}$	–	2.5	10	μs	
Output voltage Negative clamp	$-V_{QF}$	–	1.4	1.8	V	$I_Q = -2.0$ A

## Power Clamp Diode ( $V_S = 42$ V; $S_1$ open)

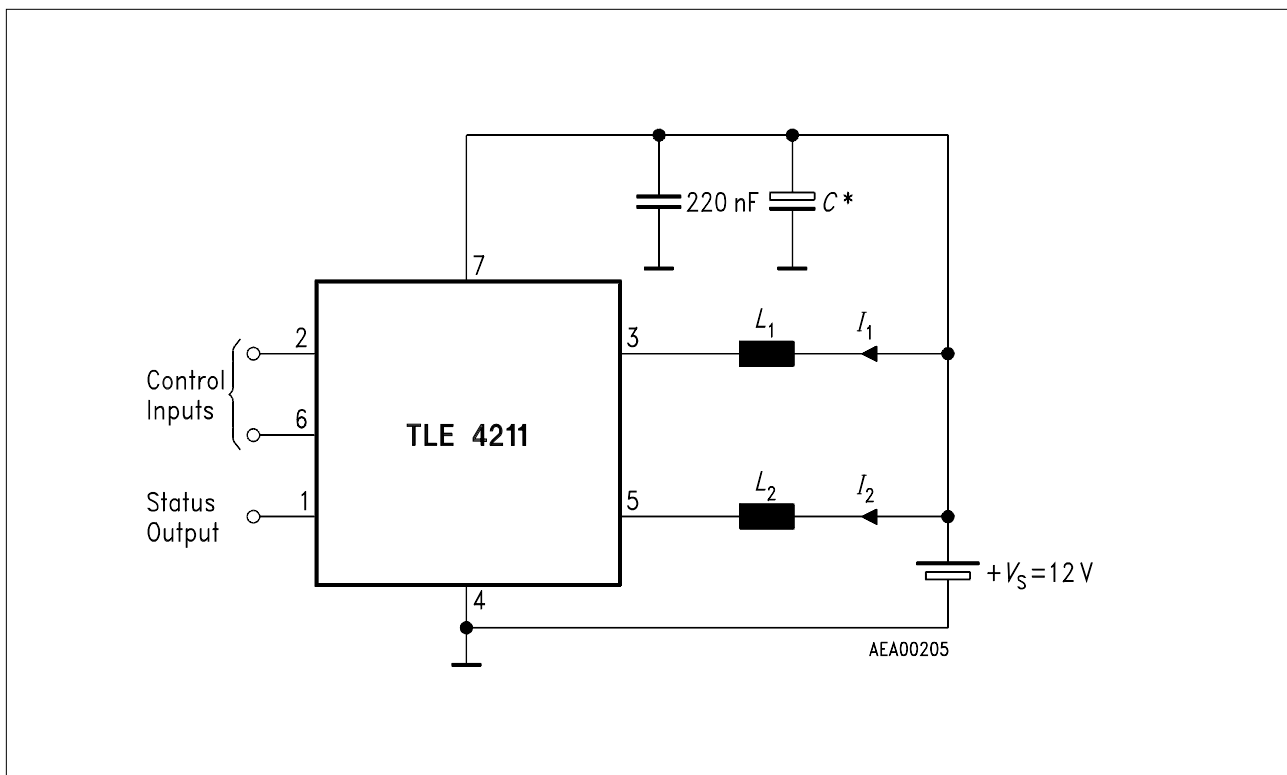
Output voltage positive clamp	$V_{QZ}$	34	36	40	V	$I_Q = 0.1$ A
Serial resistance	$r_z$	–	2	–	Ω	$0$ A $< I_Q < 2$ A



**Test Circuit**



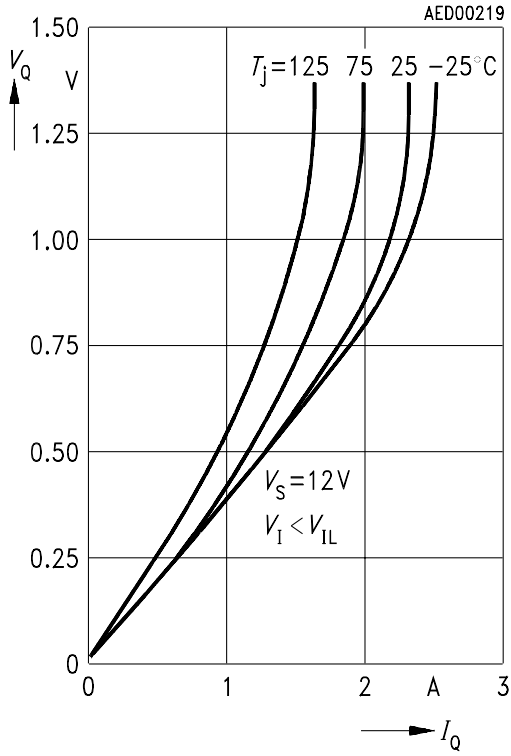
**Timing Diagram**



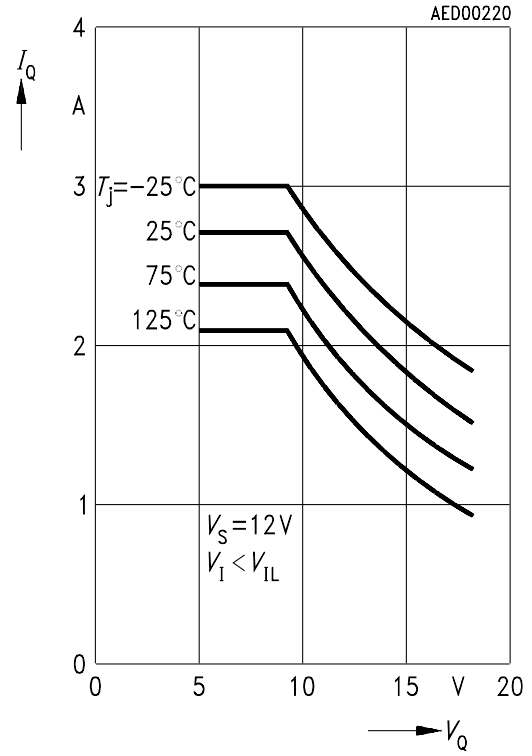
**Application Circuit**

$C^*$  is to be dimensioned such that e.g. in case of a battery voltage failure the maximum ratings of the IC are not exceeded by the recirculation energy  $L_1, L_2$ .

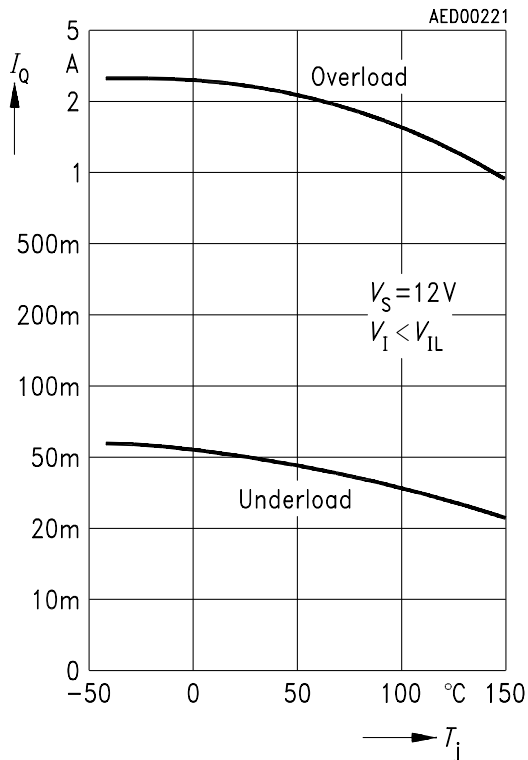
**Output Voltage  $V_Q$   
versus Output Current  $I_Q$**



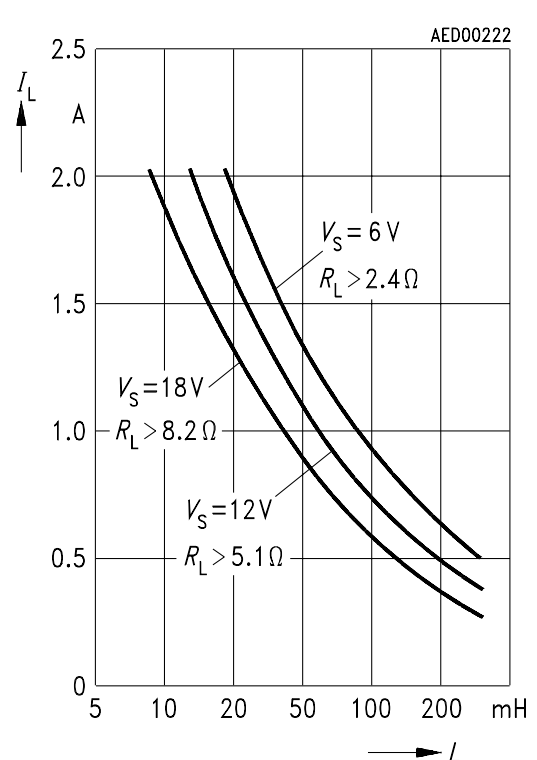
**Shorted Load Current  $I_{Q0}$   
versus Output Voltage  $V_Q$**



**Status Signal Threshold  
versus Chip Temperature  $T_j$**



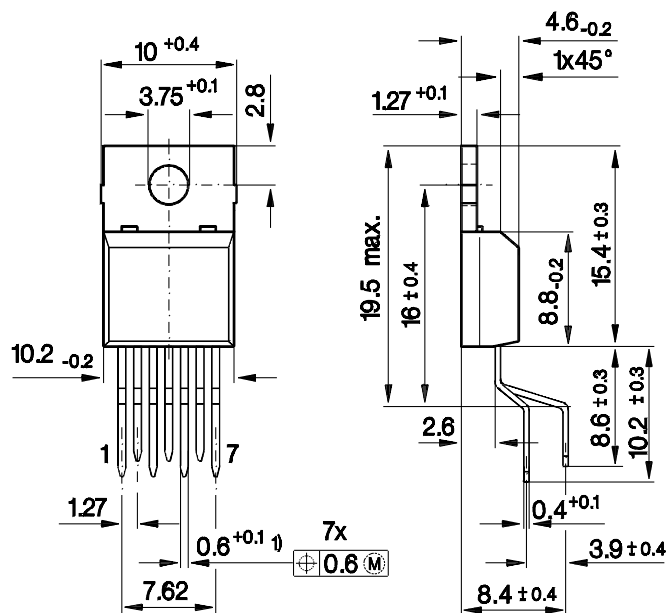
**Maximum Load Current  $I_L$   
versus Load Inductance  $L$**



## Package Outlines

### P-TO220-7-1

(Plastic Transistor Single Outline)



- 1) 0.75<sup>-0.16</sup> at dam bar (max. 1.8 from body)
- 1) 0.75<sup>-0.16</sup> Im Dichtstegbereich (max. 1.8 vom Körper)

GPT05108

### Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

SMD = Surface Mounted Device

Dimensions in mm